

FIG. 1

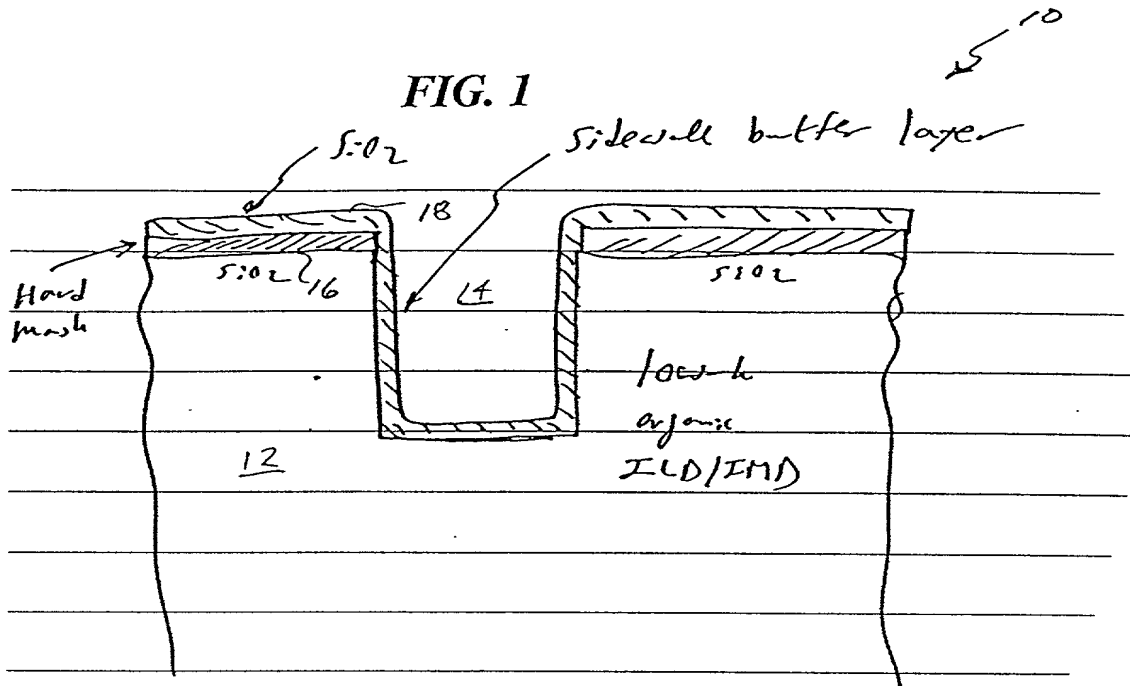
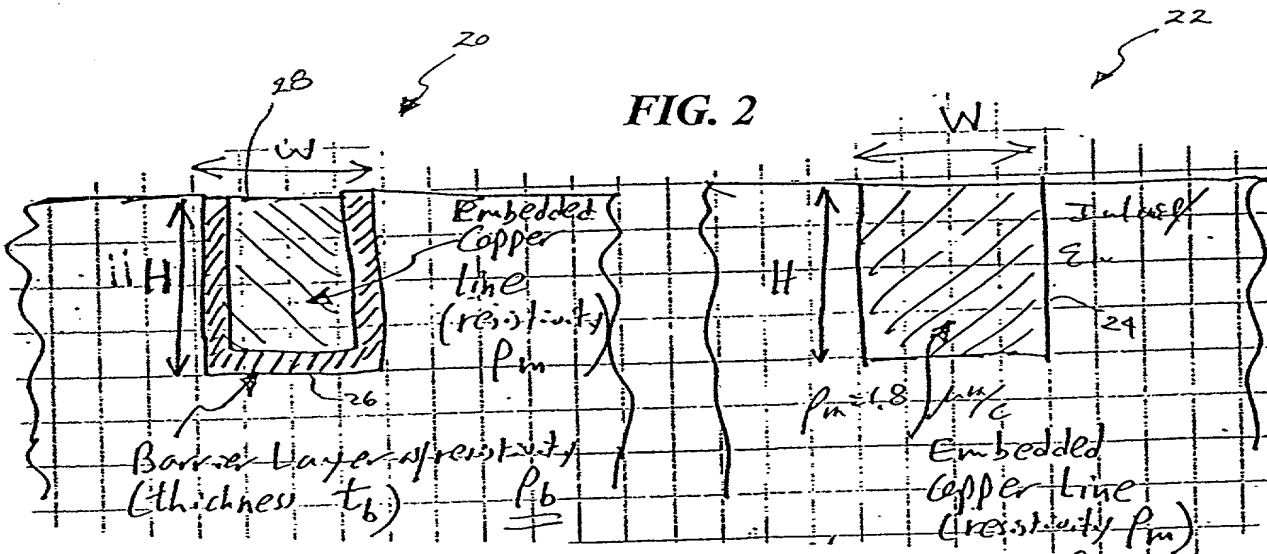


FIG. 2



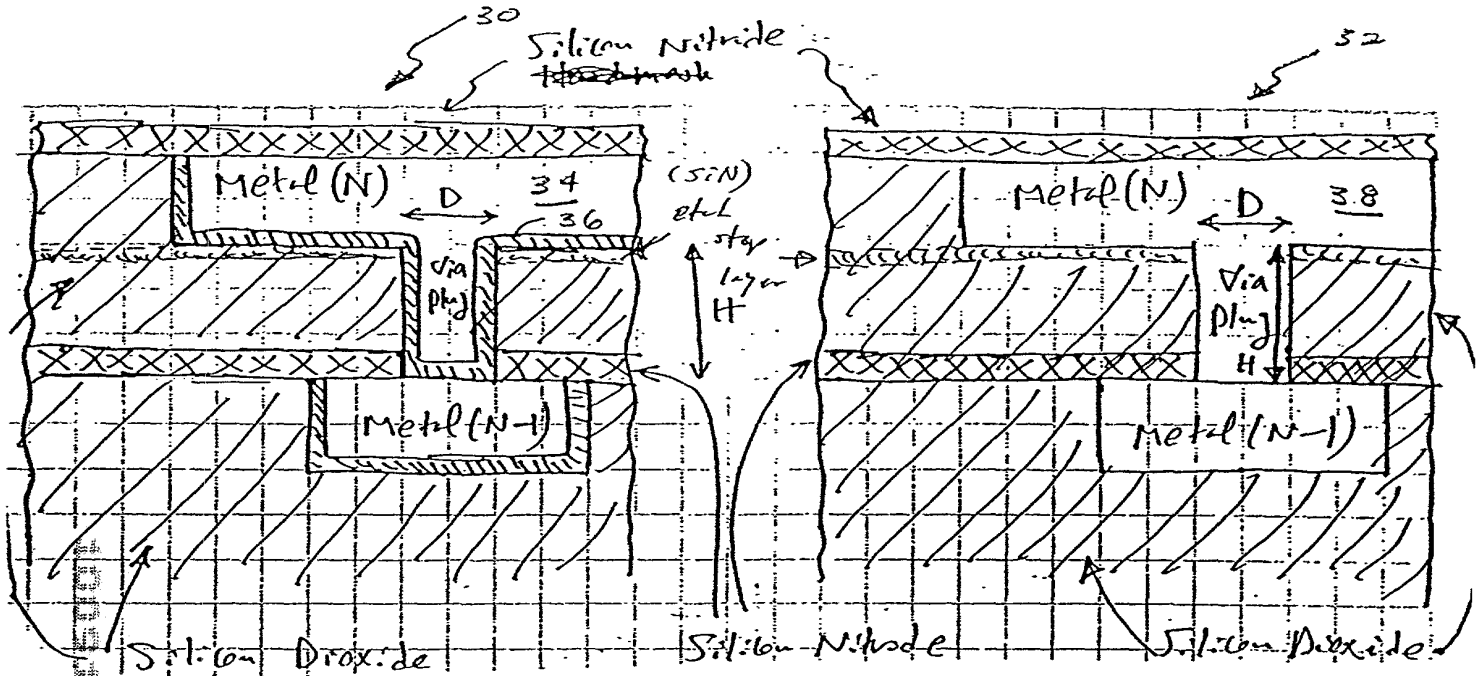


FIG. 3

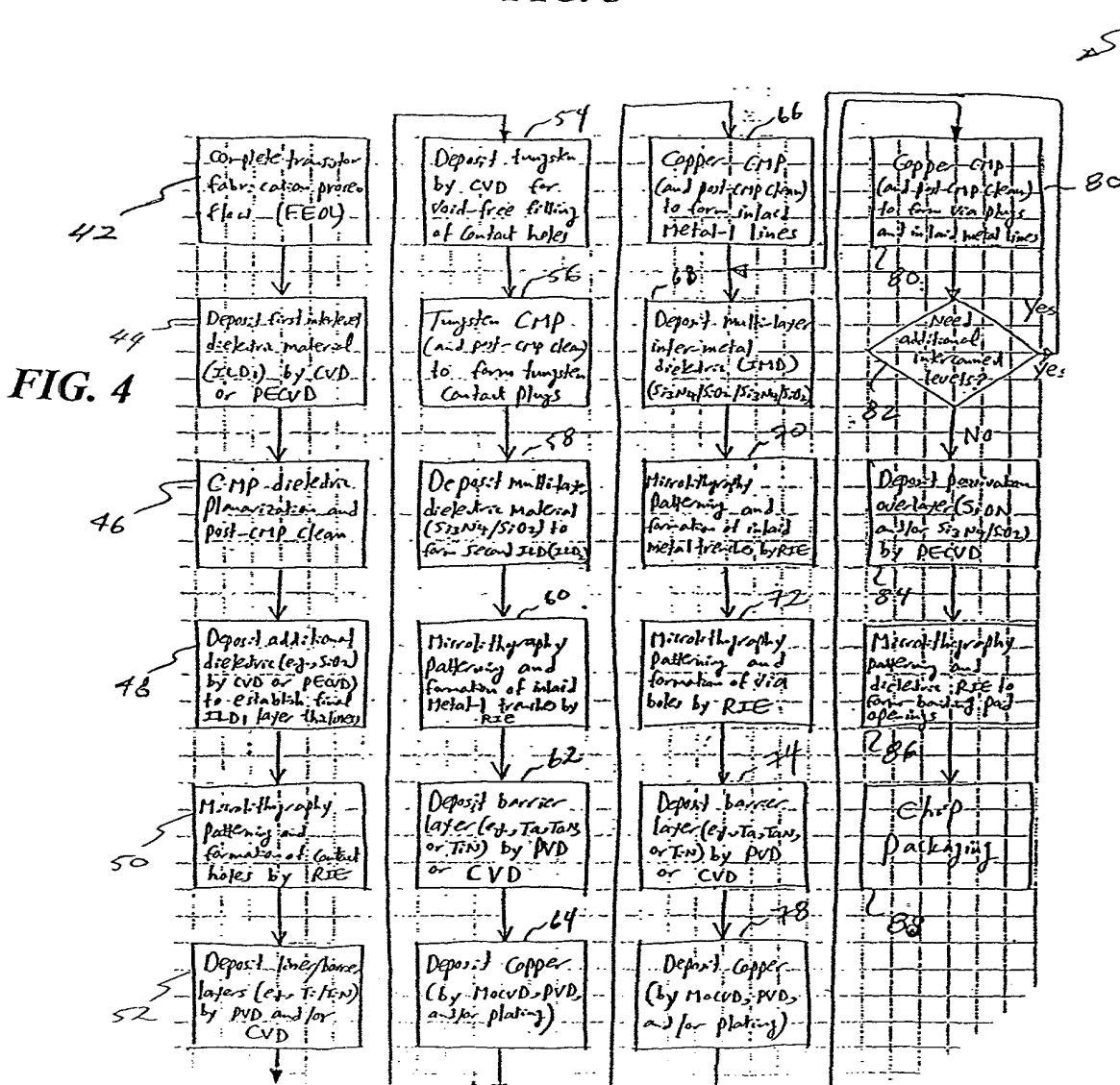


FIG. 5

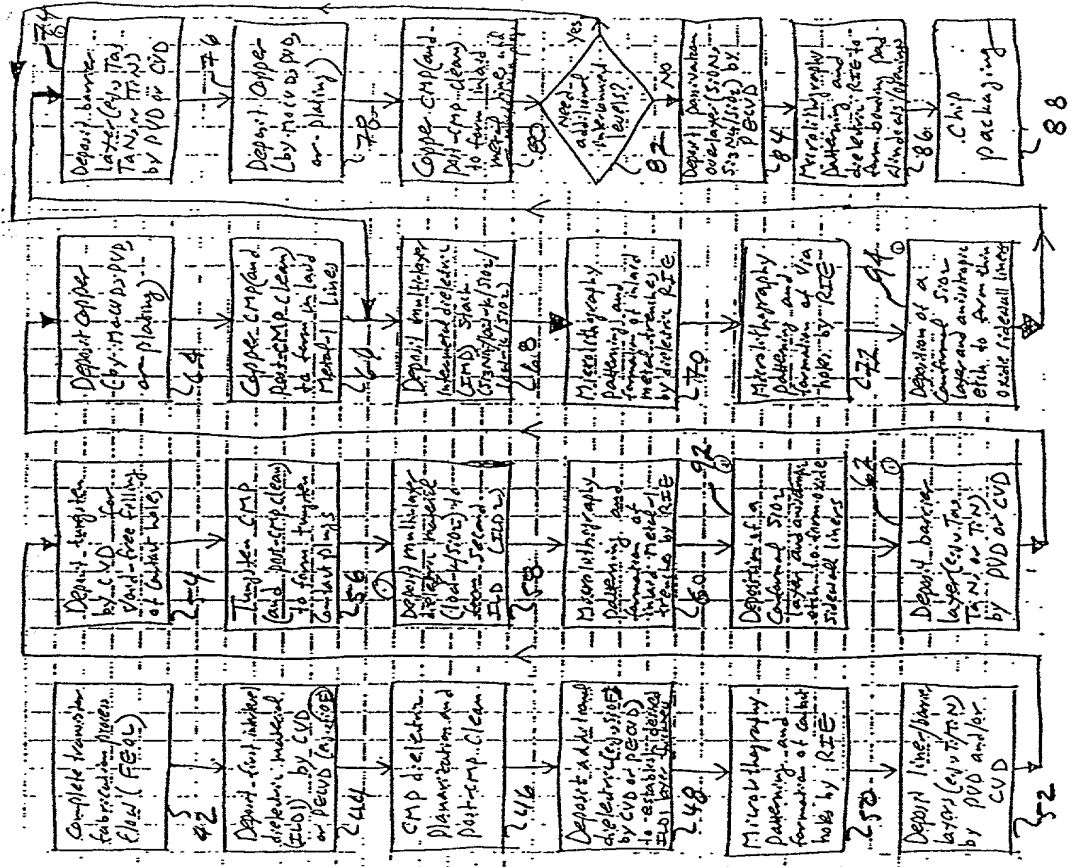
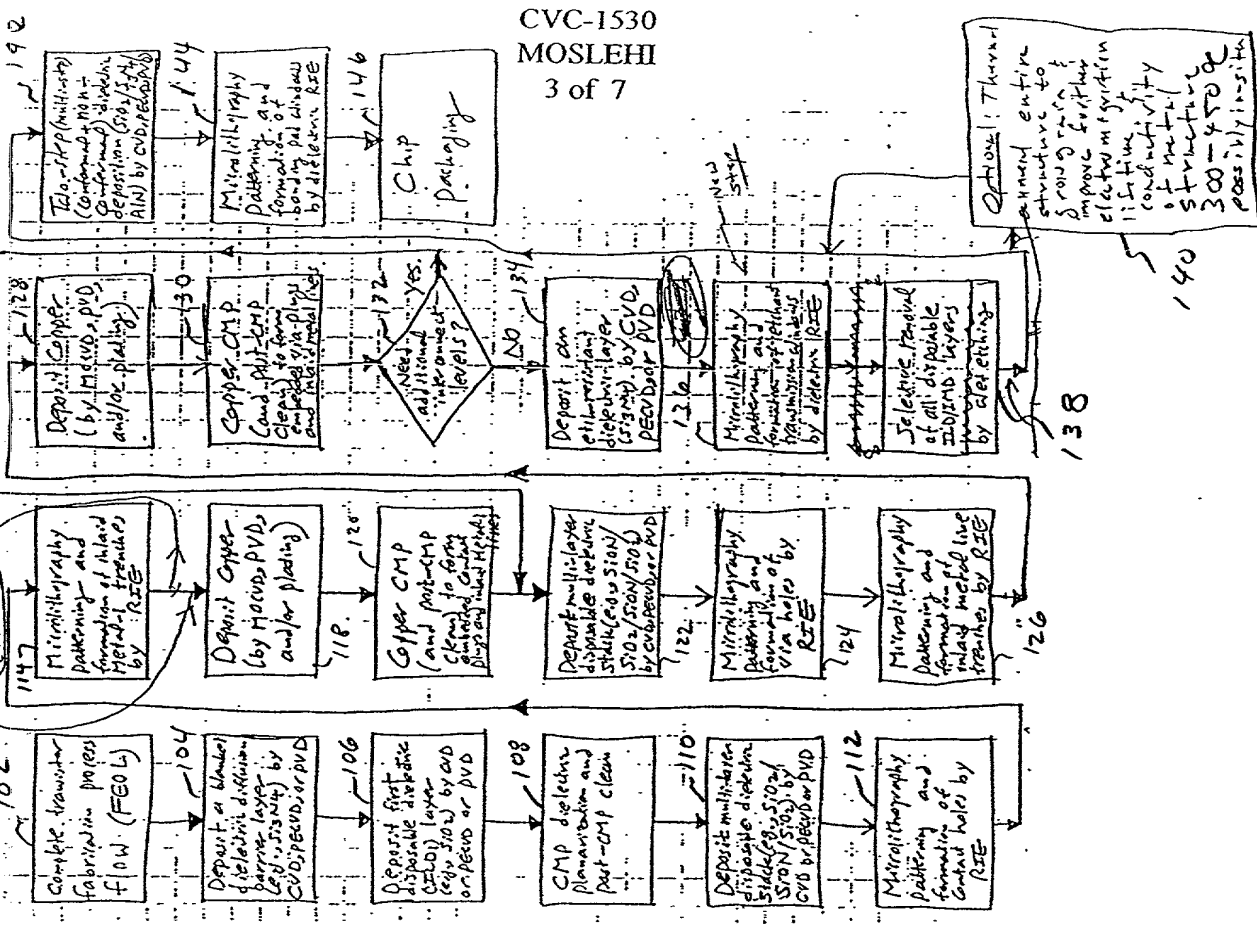
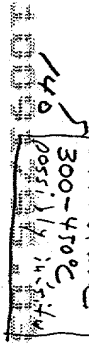


FIG. 6



Optimize: Thermal expand entire structure to grow range, improve for high electron migration, increasing conductivity of metal structure 300-450°C possibly in situ



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FIG. 10

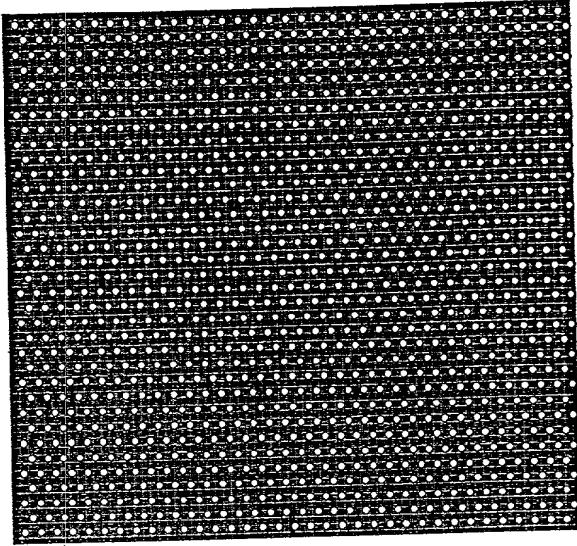


FIG. 9

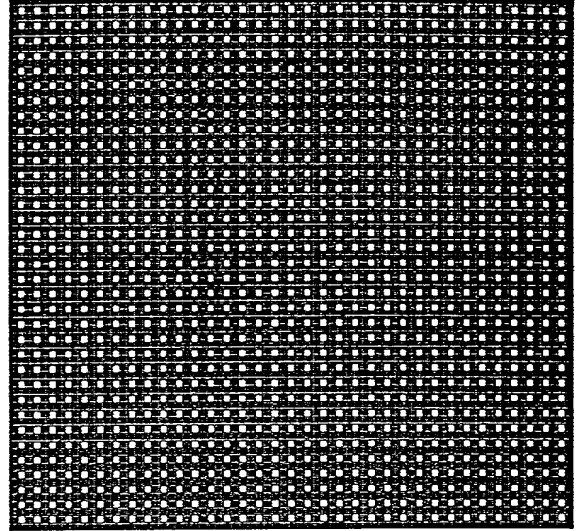


FIG. 12

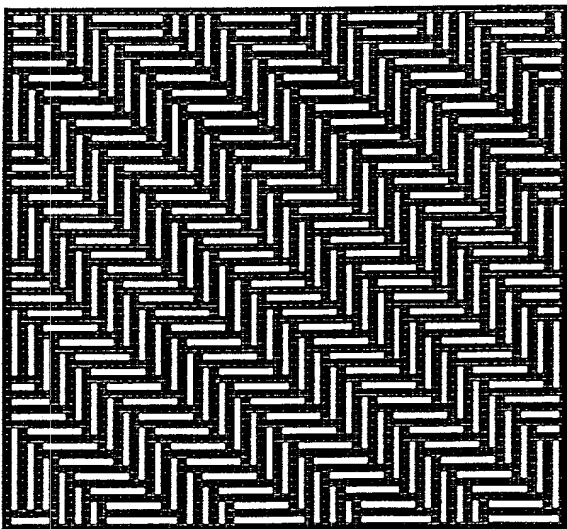
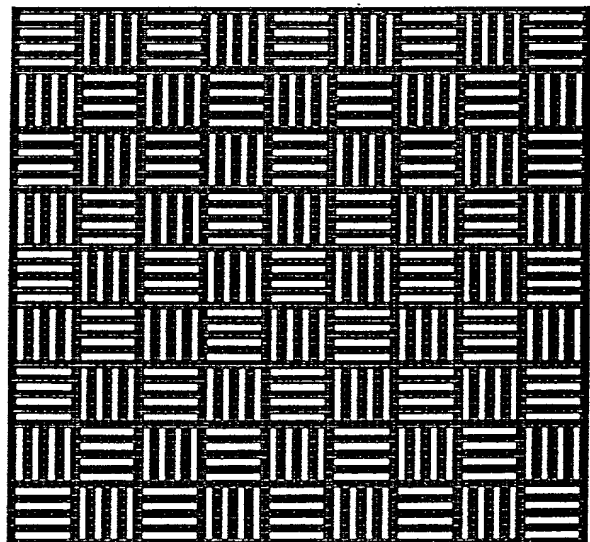


FIG. 11



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FIG. 13

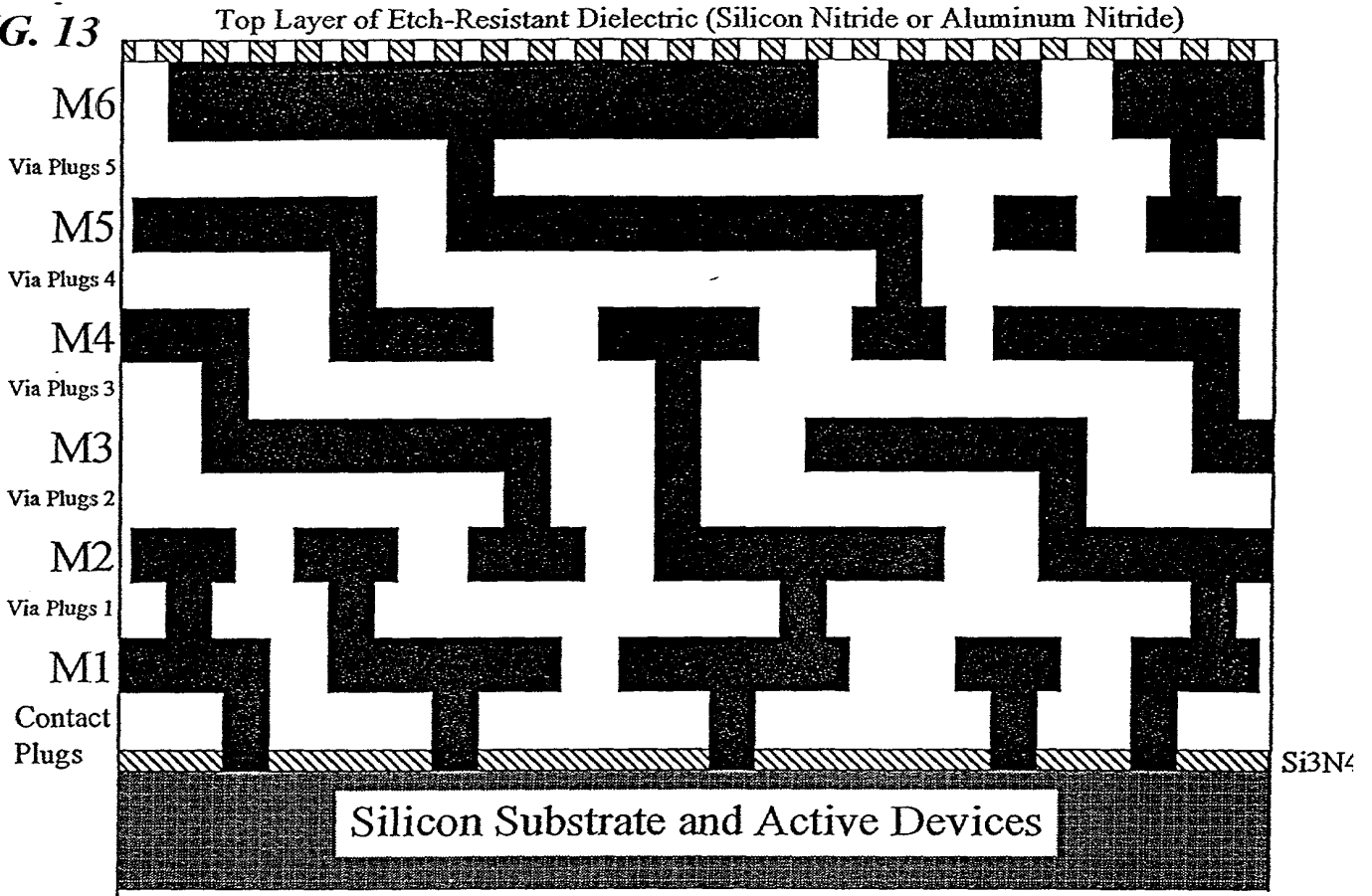
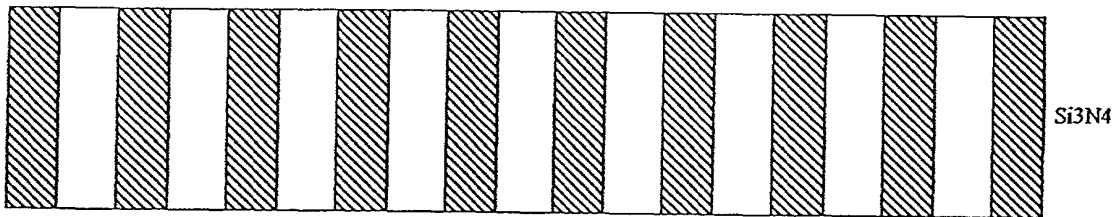


FIG. 14

Top dielectric layer (e.g., Si₃N₄) with etchant transmission windows (e.g., minimum geometry holes)



Hermetic Sealing Process

After conformal deposition of first dielectric (e.g., CVD SiO₂ or or Si₃N₄ or AlN) followed by non-conformal deposition of second sealing dielectric (e.g., PVD of AlN or DLC or Si₃N₄)

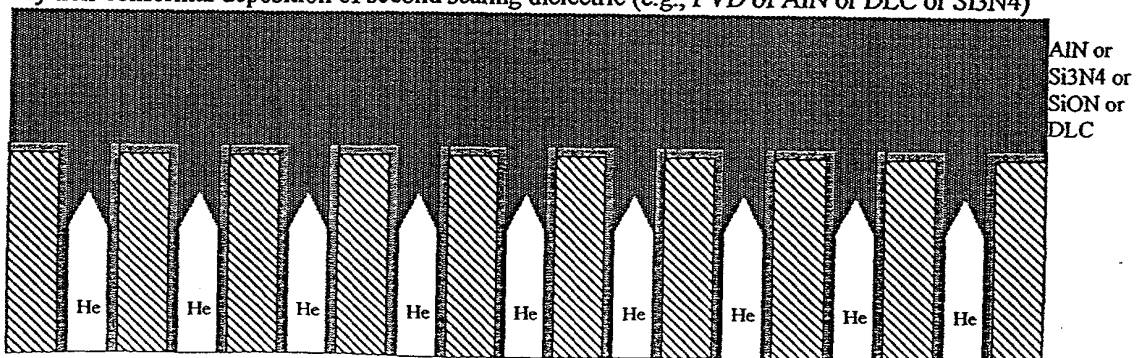


FIG. 15

